

Description

The IRFH5302TRPBF uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

V_{DS} = 30V I_D =150A

 $R_{DS(ON)} < 2.4 \text{m}\Omega \text{ V}_{GS} = 10 \text{V}$

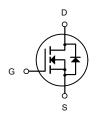
Application

Battery protection

Load switch

Uninterruptible power supply

DFN5X6-8L (PQFN-8(5x6))



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
IRFH5302TRPBF	DFN5X6-8L(PQFN-8(5x6))	FH5302 XXXX	5000

Absolute Maximum Ratings (Tc=25 ℃ unless otherwise noted)

Symbol	Parameter	Rating	Units
Vos	Drain-Source Voltage	30	V
Vgs	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	150	А
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ 10V ¹	80	Α
Ірм	Pulsed Drain Current ²	160	А
EAS	Single Pulse Avalanche Energy ³	180	mJ
las	Avalanche Current 60		Α
P _D @T _C =25°C	Total Power Dissipation ⁴	Total Power Dissipation ⁴ 187	
Тѕтс	Storage Temperature Range -55 to 150		°C
TJ	T _J Operating Junction Temperature Range -55 to 19		°C
Reja	Thermal Resistance Junction-Ambient ¹ 62		°C/W
Rыс	Thermal Resistance Junction-Case ¹	1.1	°C/W



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30			V	
△BV _{DSS} /△T _J	BV _{DSS} Temperature Coefficient	Reference to 25°C , I _D =1mA		0.014		V/°C	
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =30A		2	2.4	mO	
	Static Drain-Source On-Resistance	V _{GS} =4.5V , I _D =15A		2.5	3.2	mΩ	
V _{GS(th)}	Gate Threshold Voltage		1.2		2.5	V	
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	$V_{GS}=V_{DS}$, $I_D=250uA$		-4		mV/°C	
I _{DSS}	Dunin Course Lookens Courset	V _{DS} =24V , V _{GS} =0V , T _J =25°C			1	uA	
	Drain-Source Leakage Current	V _{DS} =24V , V _{GS} =0V , T _J =55°C			5		
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V			±100	nA	
gfs	Forward Transconductance	V _{DS} =5V , I _D =30A		50		S	
Rg	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		1.7		Ω	
Qg	Total Gate Charge (4.5V)			56.9			
Qgs	ate-Source Charge V _{DS} =15V , V _{GS} =10V , I _D =15A			13.8		nC	
Q_{gd}	Gate-Drain Charge			23.5		1	
$T_{d(on)}$	Turn-On Delay Time			20.1			
Tr	Rise Time	V_{DD} =15V , V_{GS} =10V , R_{G} =3.3 Ω ,		6.3]	
$T_{d(off)}$	Turn-Off Delay Time	I _D =1A		124.6		ns	
Tf	Fall Time			15.8			
Ciss	Input Capacitance			4345			
Coss	Output Capacitance V _{DS} =15V , V _{GS} =0V , f=1MHz			340		pF	
Crss	Reverse Transfer Capacitance			225			
ls	Continuous Source Current ^{1,6}	V _G =V _D =0V , Force Current			150	Α	
V_{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =1A , T _J =25°C			1.2	V	

Note:

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2%
- 3. The EAS data shows Max. rating . The test condition is V_{DD} =25V, V_{GS} =10V, L=0.1mH, I_{AS} =60A
- 4.The power dissipation is limited by 150°C junction temperature
- 5. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.
- 6.Package limitation current is 85A.

Typical Characteristics

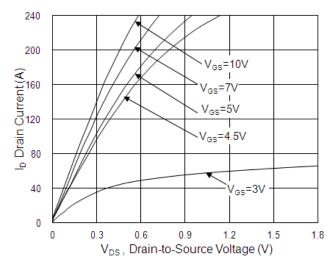


Fig.1 Typical Output Characteristics

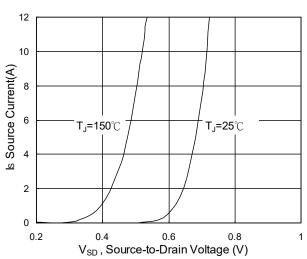


Fig.3 Forward Characteristics of Reverse

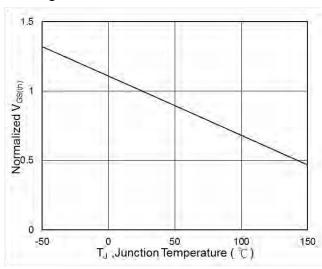


Fig.5 Normalized $V_{\text{GS(th)}}$ v.s T_{J}

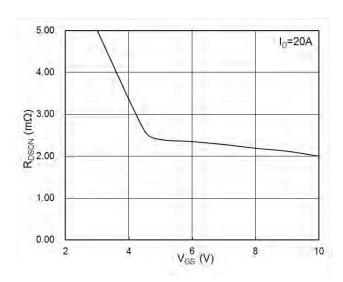


Fig.2 On-Resistance v.s Gate-Source

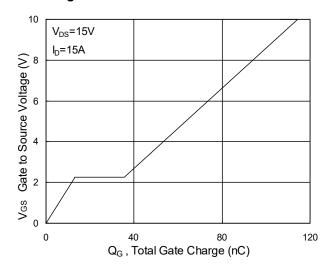


Fig.4 Gate-Charge Characteristics

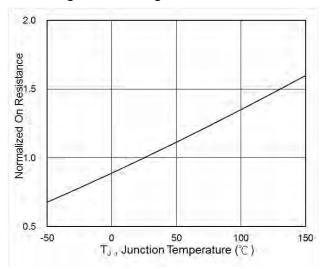
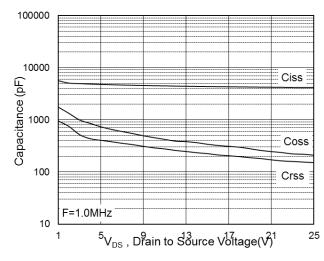


Fig.6 Normalized R_{DSON} v.s T_J



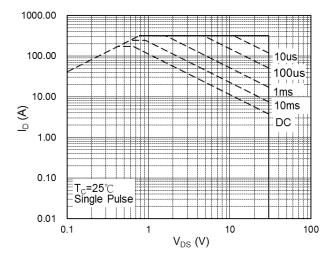


Fig.7 Capacitance

Fig.8 Safe Operating Area

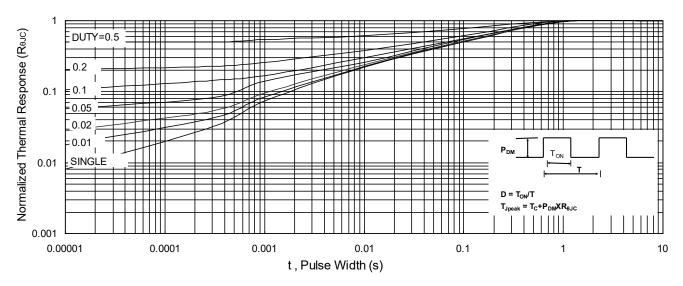
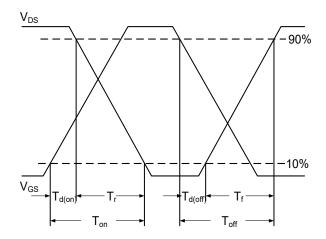


Fig.9 Normalized Maximum Transient Thermal Impedance





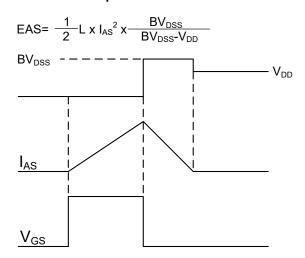
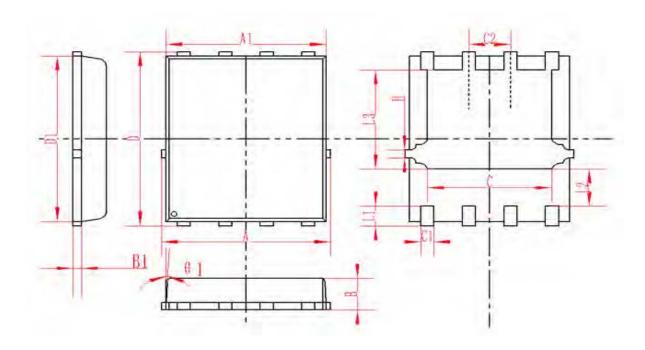


Fig.11 Unclamped Inductive Switching Waveform



DFN5X6-8L(PQFN-8(5x6))Package Information



SYMBOL	MM		INCH				
	MIN	NOM	MAX	MIN	NOM	MAX	
А	4.95	5	5.05	0.195	0.197	0.199	
A1	4.82	4.9	4.98	0.190	0.193	0.196	
D	5.98	6	6.02	0.235	0.236	0.237	
D1	5.67	5.75	5.83	0.223	0.226	0.230	
В	0.9	0.95	1	0.035	0.037	0.039	
B1	0.254REF		0.010REF				
С	3.95	4	4.05	0.156	0.157	0.159	
C1	0.35	0.4	0.45	0.014	0.016	0.018	
C2	1.27TYP		0.5TYP				
θ1	8°	10°	12°	8°	10°	12°	
L1	0.63	0.64	0.65	0.025	0.025	0.026	
L2	1.2	1.3	1.4	0.047	0.051	0.055	
L3	3.415	3.42	3.425	0.134	0.135	0.135	
Н	0.24	0.25	0.26	0.009	0.010	0.010	



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